

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
650V	35mΩ@10V	77A

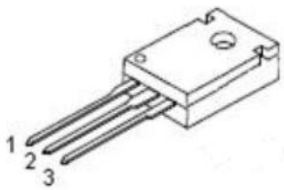
Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

Applications

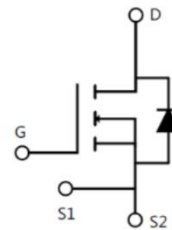
- PD charger
- Large screen display
- Telecom power
- Server power

Package

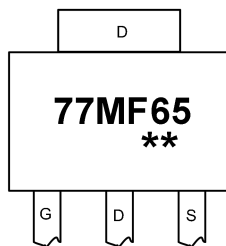


TO-247(1:G 2:D 3:S)

Circuit diagram



Marking



77MF65 : Product code
** : Month code

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain source voltage	V_{DS}	650	V
Gate source voltage	V_{GS}	± 30	V
Continuous drain current(Tc=25°C)	I_D	77	A
Continuous drain current(Tc=100°C)	I_D	45	A
Pulsed drain current	I_{DM}	308	A
Power dissipation(Tc=25°C)	P_D	400	W
Single pulsed avalanche energy ¹⁾	E_{AS}	1950	mJ
Thermal resistance, junction-case	$R_{\theta JC}$	0.31	°C/W
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Electrical characteristics (Ta=25°C, unless otherwise noted)

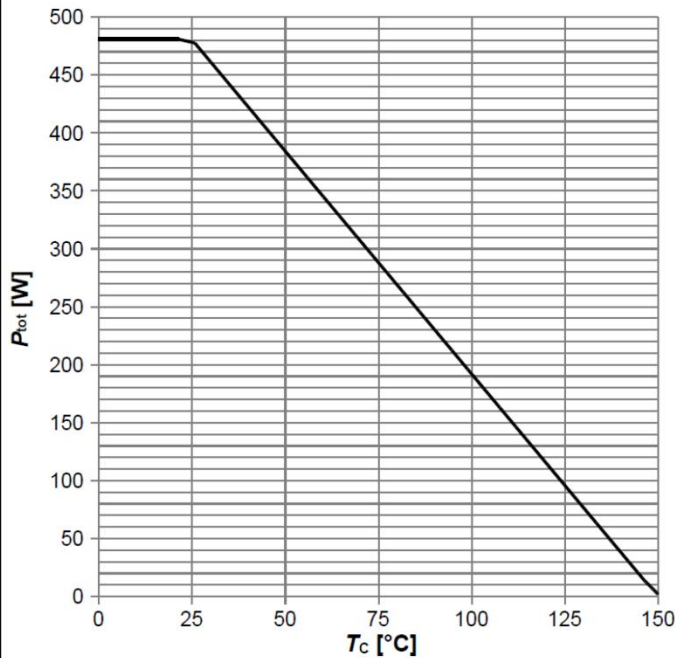
Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu A, V_{GS} = 0V$	650	-	-	V
Drain Cut-Off Current	I_{DSS}	$V_{DS} = 480V, V_{GS} = 0V$	-	-	1	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 0.1	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	3.5	4.5	V
Drain-Source ON Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 35A$	-	35	41	m Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	-	6200	-	pF
Output Capacitance	C_{oss}		-	340	-	
Reverse Transfer Capacitance	C_{rss}		-	14	-	
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 520V, V_{GS} = 10V, I_D = 35A$	-	294	-	nC
Gate-Source Charge	Q_{gs}		-	55	-	
Gate-Drain Charge	Q_{gd}		-	190	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 520V, I_D = 35A, R_G = 20\Omega$	-	39	-	ns
Rise Time	t_r		-	20	-	
Turn-Off Delay Time	$t_{d(off)}$		-	90	-	
Fall Time	t_f		-	5	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	$I_S = 1A, V_{GS} = 0V$	-	-	1.2	V
Reverse Recovery Time	T_{rr}	$V_R = 400V, I_S = 10A, di/dt = 100A/\mu s$	-	186	-	ns

Note:

- E_{AS} is tested at starting $T_j = 25^\circ C, V_{DD} = 100V, V_{GS} = 10V, L = 0.5mH, R_g = 25\Omega$;

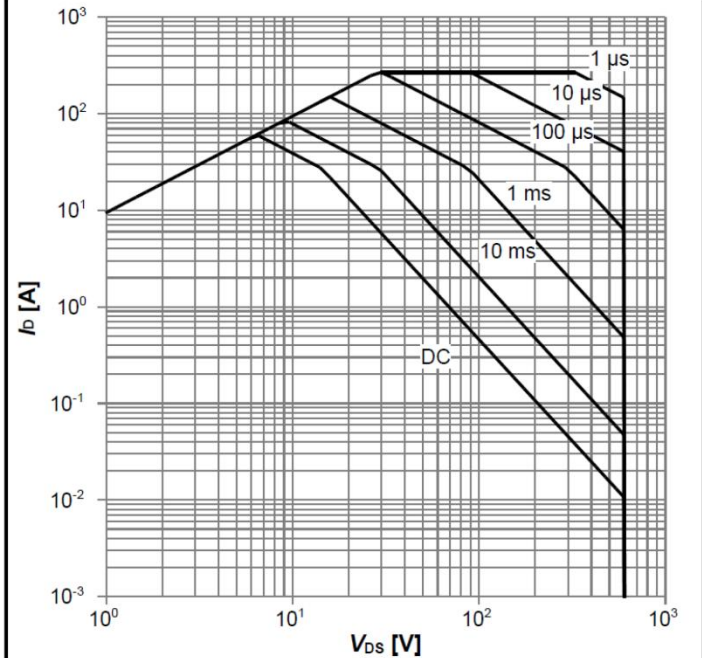
Typical Characteristics

Diagram 1: Power dissipation



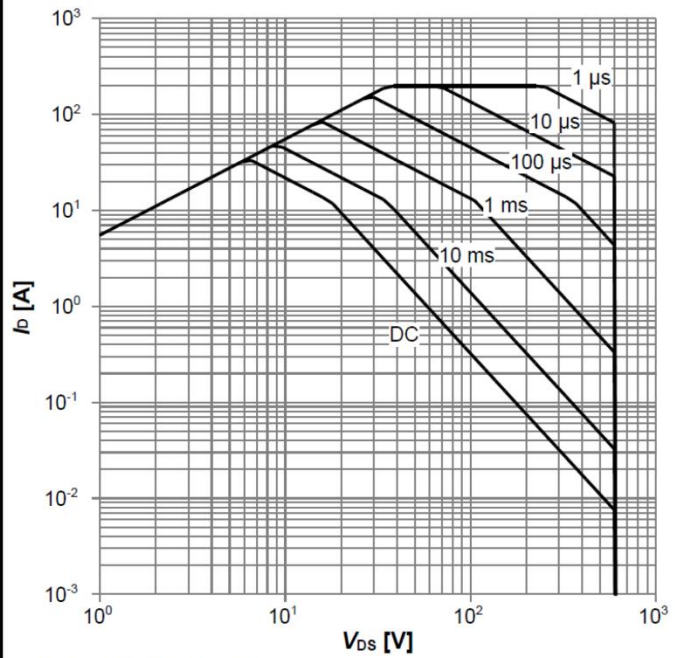
$P_{tot}=f(T_c)$

Diagram 2: Safe operating area



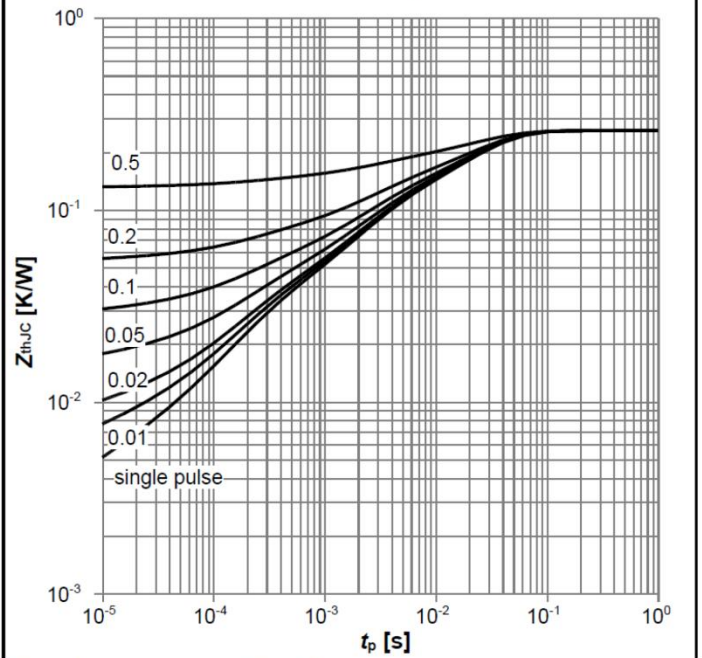
$I_D=f(V_{DS}); T_c=25\text{ }^\circ\text{C}; D=0; \text{parameter: } t_p$

Diagram 3: Safe operating area



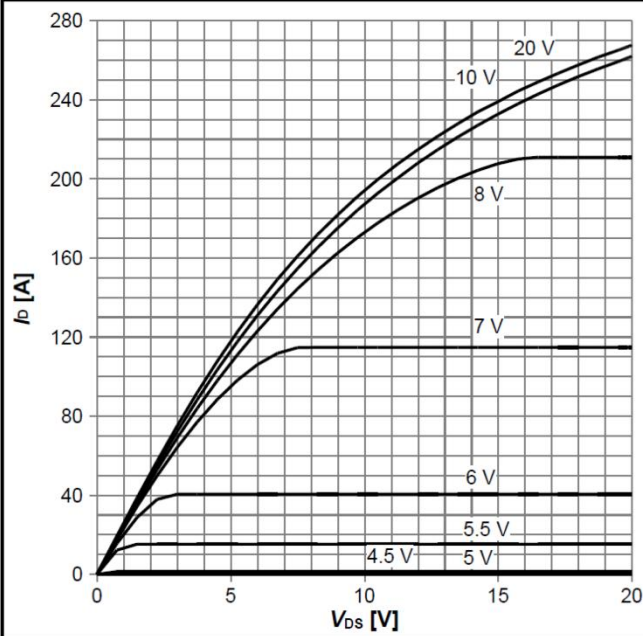
$I_D=f(V_{DS}); T_c=80\text{ }^\circ\text{C}; D=0; \text{parameter: } t_p$

Diagram 4: Max. transient thermal impedance



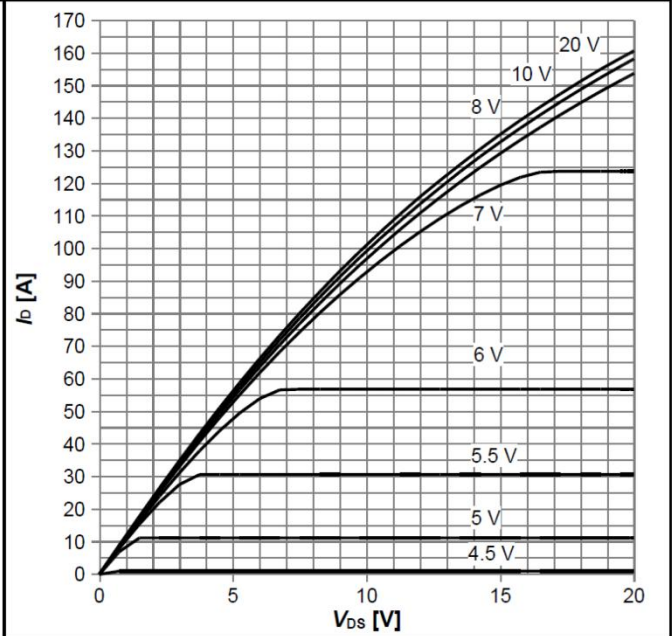
$Z_{thJC}=f(t_p); \text{parameter: } D=t_p/T$

Diagram 5: Typ. output characteristics



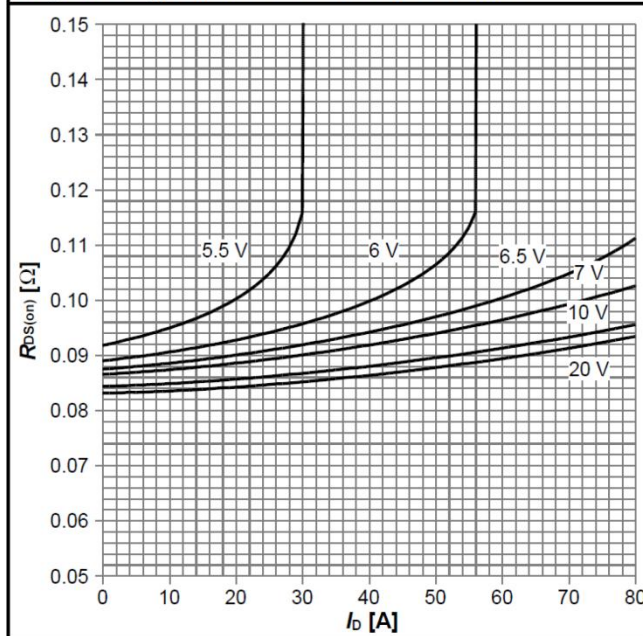
$I_D=f(V_{DS}); T_J=25\text{ }^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 6: Typ. output characteristics



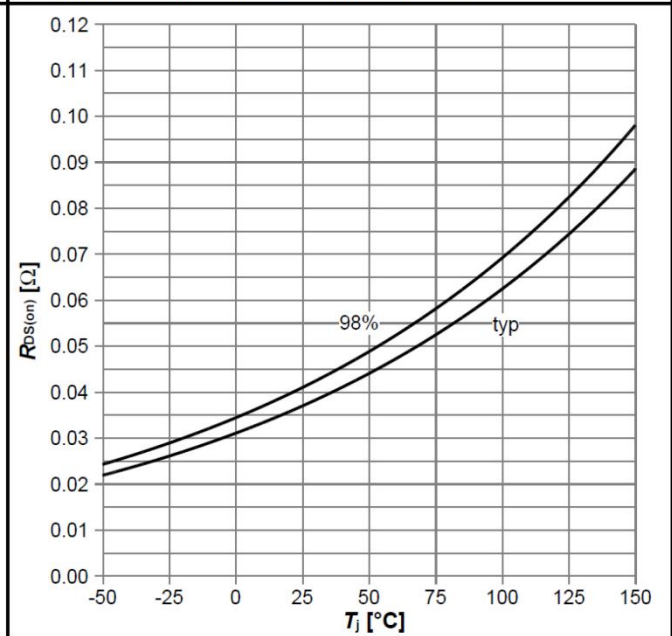
$I_D=f(V_{DS}); T_J=125\text{ }^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. drain-source on-state resistance



$R_{DS(on)}=f(I_D); T_J=125\text{ }^\circ\text{C}; \text{parameter: } V_{GS}$

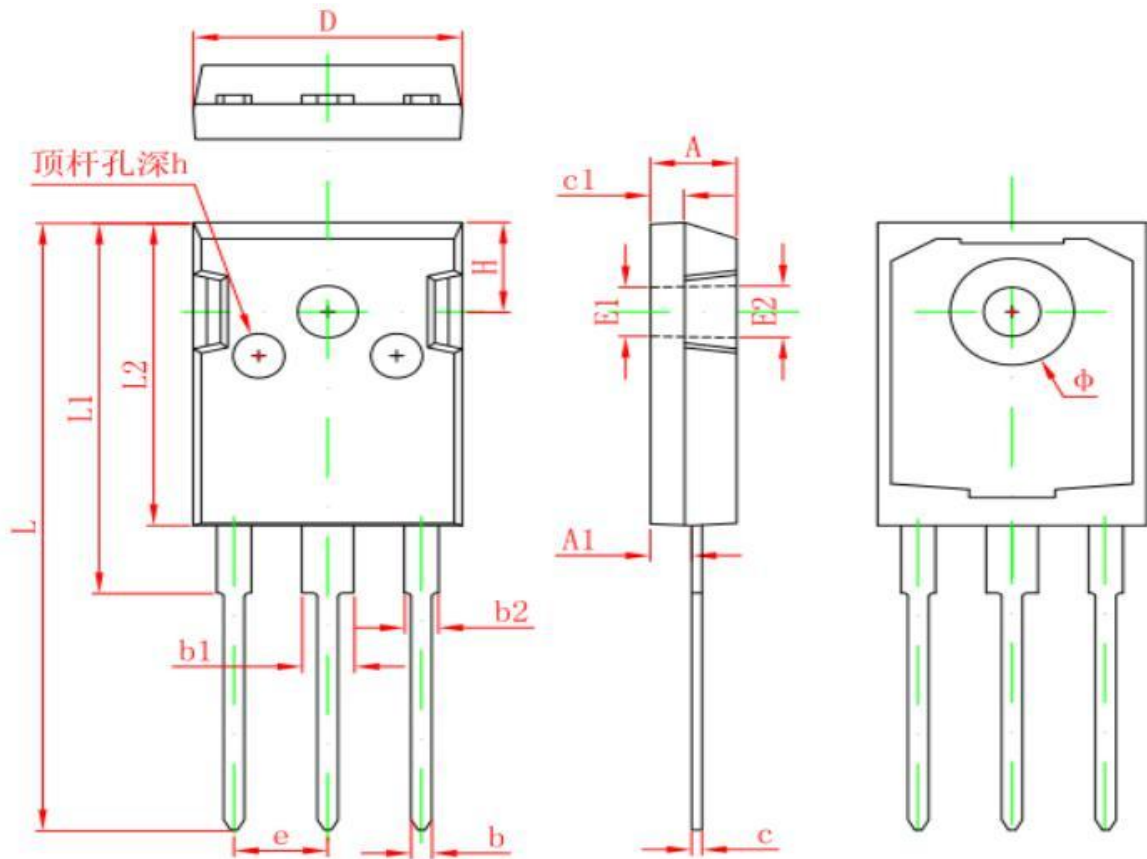
Diagram 8: Drain-source on-state resistance



$R_{DS(on)}=f(T_J); I_D=35.5\text{ A}; V_{GS}=10\text{ V}$



TO-247 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF.		0.138 REF.	
E2	3.600 REF.		0.142 REF.	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP.		0.215 TYP.	
H	5.980 REF.		0.235 REF.	
h	0.000	0.300	0.000	0.012

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